

isc Silicon NPN Power Transistor

BU608D

DESCRIPTION

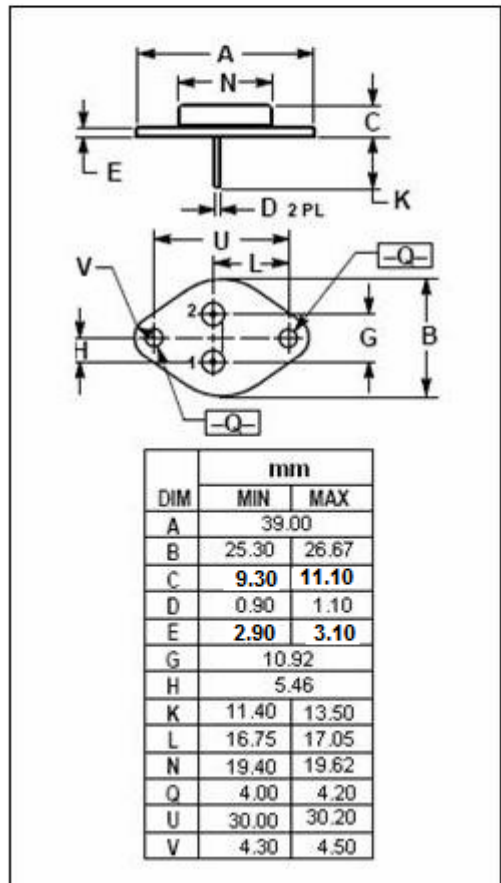
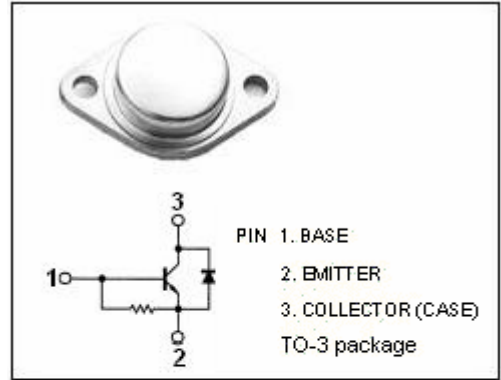
- High Voltage: $V_{CEV} = 400V(\text{Min})$
- Fast Switching Speed-
: $t_f = 0.5 \mu s(\text{Max})$
- Low Saturation Voltage-
: $V_{CE(\text{sat})} = 1.0V(\text{Max}) @ I_C = 6A$

APPLICATIONS

- Designed for use in horizontal deflection output stages of TV's and CRT's

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEV}	Collector-Emitter Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ C$	90	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



isc Silicon NPN Power Transistor**BU608D****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C= 100\text{mA}; I_B= 0$	200			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 6\text{A}; I_B= 1.2\text{A}$			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C= 6\text{A}; I_B= 1.2\text{A}$			1.5	V
h_{FE}	DC Current Gain	$I_C= 2\text{A}; V_{CE}= 5\text{V};$		15		
I_{CEV}	Collector Cutoff Current	$V_{CE}= 400\text{V}; V_{BE}= -1.5\text{V}$			15	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 6\text{V}; I_C= 0$			400	mA
f_T	Current-Gain—Bandwidth Product	$I_C= 0.5\text{A}; V_{CE}= 10\text{V}, f_{test}= 1\text{MHz}$	10			MHz
V_{ECF}	C-E Diode Forward Voltage	$I_F= 5\text{A}$			1.5	V
t_f	Fall Time	$I_C= 6\text{A}; I_{B1}= -I_{B2}= 1.2\text{A}, V_{CC}= 40\text{V}$			0.5	μs